



- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

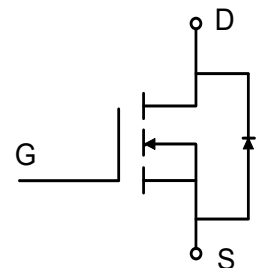
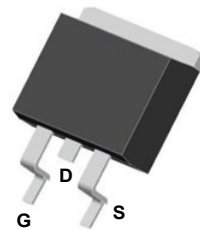
BVDSS	RDSON	ID
200V	20 mΩ	100A

Description

The XR100N20G is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XR100N20G meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	100	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	63	A
I_{DM}	Pulsed Drain Current ²	400	A
EAS	Single Pulse Avalanche Energy ³	1190	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	272	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	---	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.46	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	200	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=61A$	---	20	25.5	$m\Omega$
		$V_{GS}=4.5V$, $I_D=61A$	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	3	---	5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=150V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=150V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=31A$	---	73	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=61A$	---	134	---	nC
Q_{gs}	Gate-Source Charge		---	49.6	---	
Q_{gd}	Gate-Drain Charge		---	39.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$, $R_L=1.25\Omega$ $R_G=3\Omega$, $V_{GS}=10V$	---	36.3	---	ns
T_r	Rise Time		---	9.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	64	---	
T_f	Fall Time		---	6.3	---	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	8826	---	pF
C_{oss}	Output Capacitance		---	532	---	
C_{rss}	Reverse Transfer Capacitance		---	148	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	65	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=31A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=61A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	102	---	nS
Q_{rr}	Reverse Recovery Charge		---	550.3	---	nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=40V$, $V_G=10V$, $R_g=25\Omega$, $L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

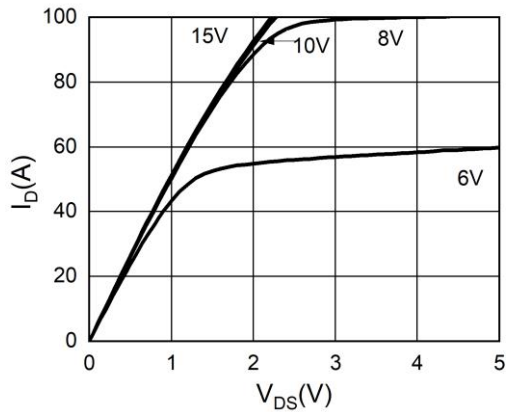


Figure 2. Transfer Characteristics

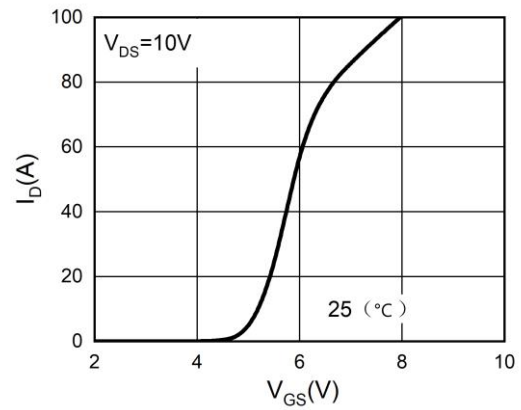


Figure 3. Power Dissipation

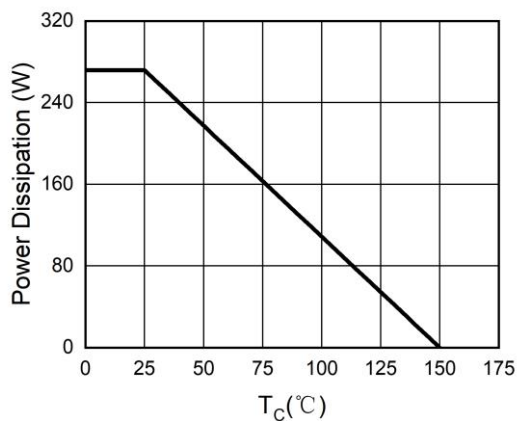


Figure 4. Drain Current

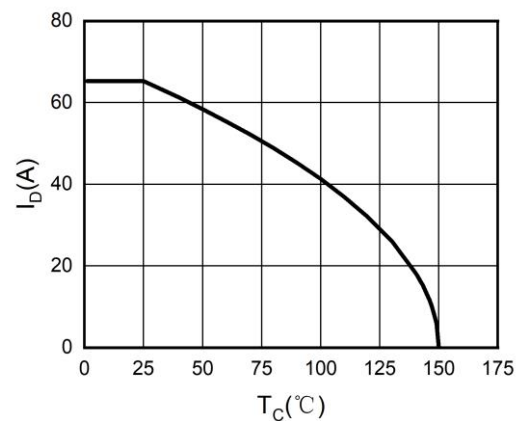


Figure 5. BV_{DSS} vs Junction Temperature

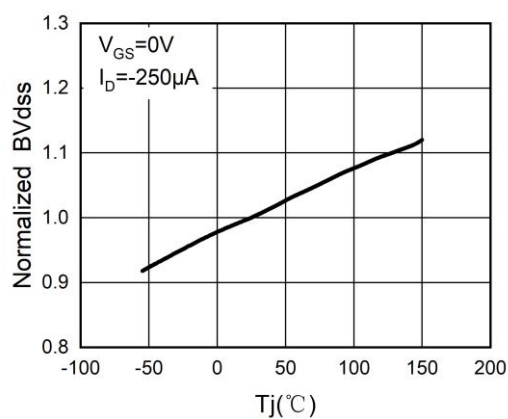
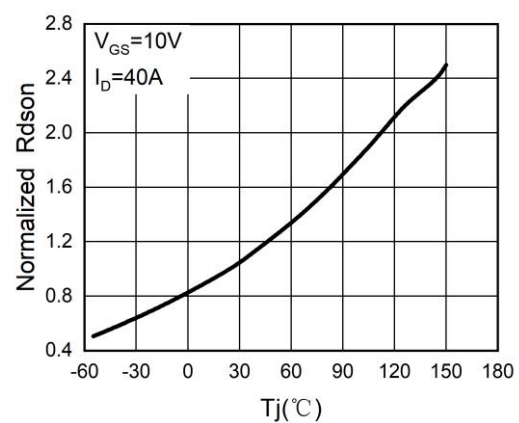


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

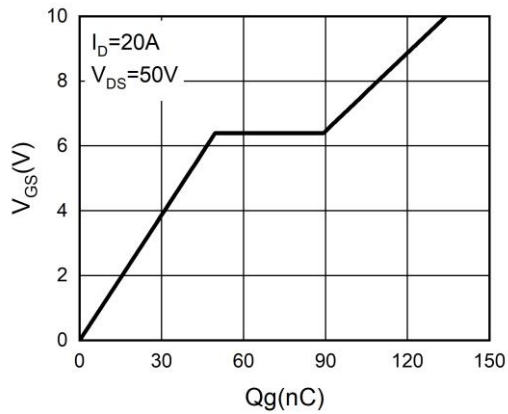


Figure 8. Capacitance

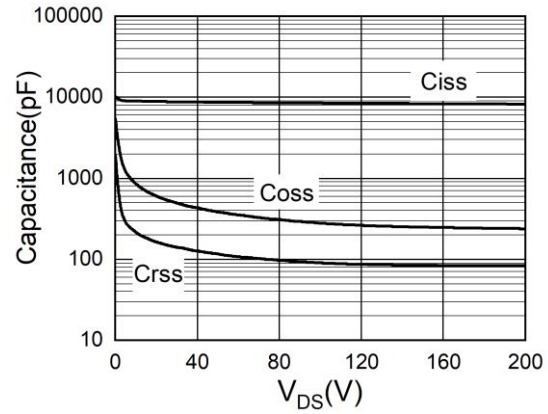


Figure 9. Body-Diode Characteristics

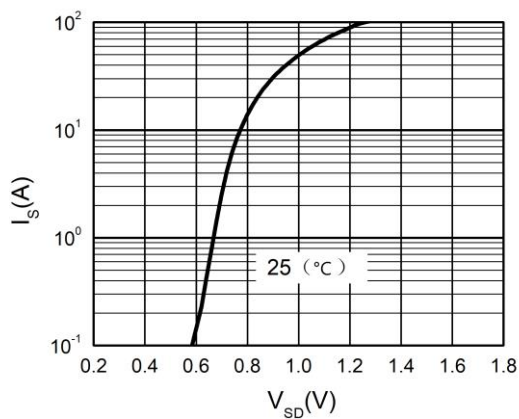
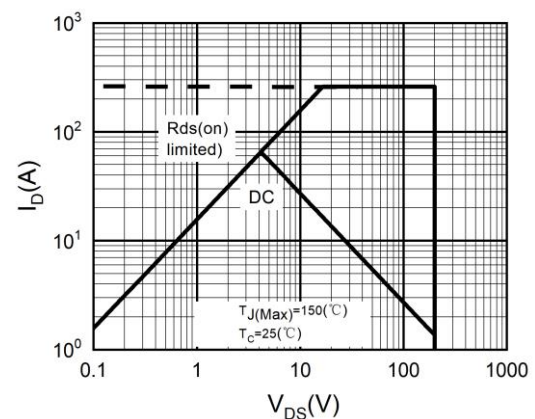
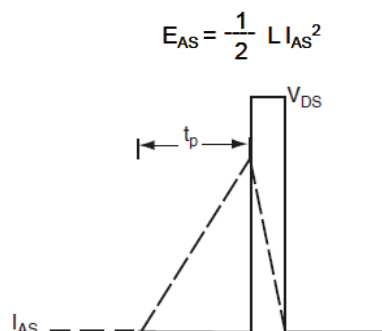
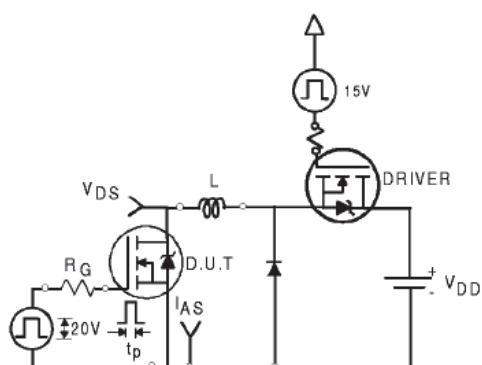


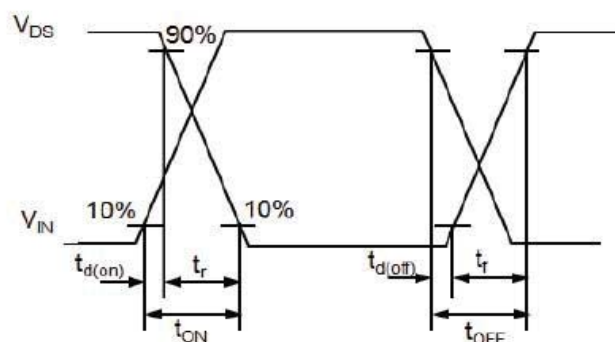
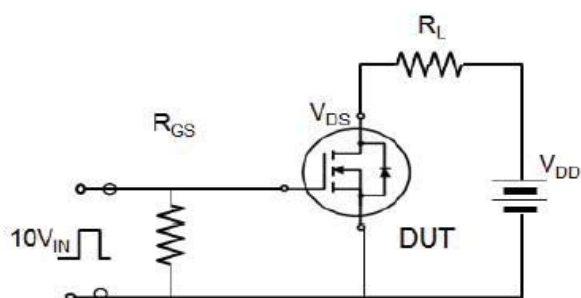
Figure 10. Maximum Safe Operating Area



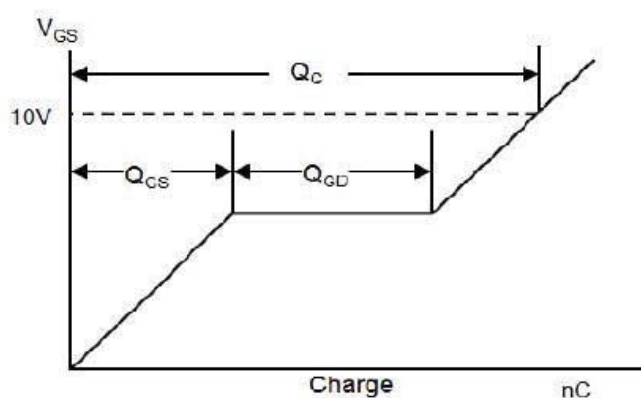
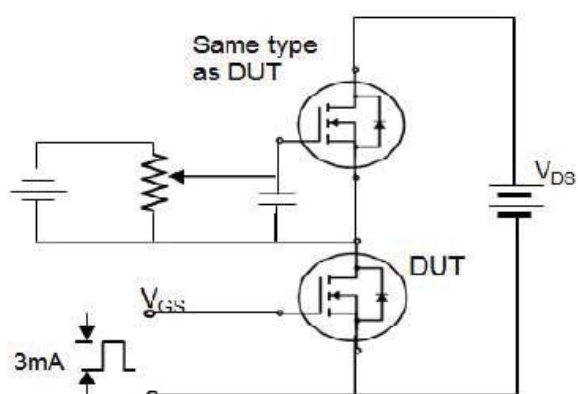
Avalanche Test Circuit



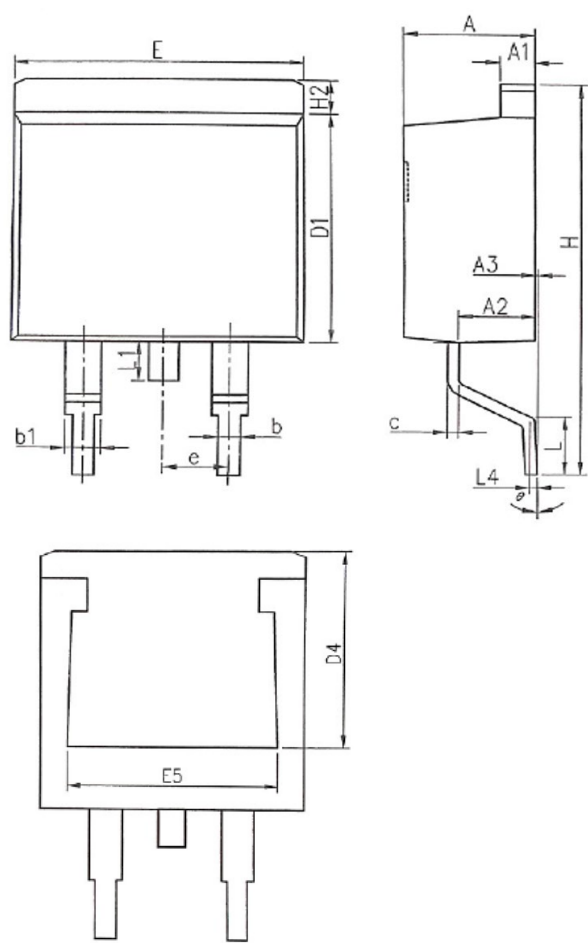
Switching Time Test Circuit



Gate Charge Test Circuit



Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°